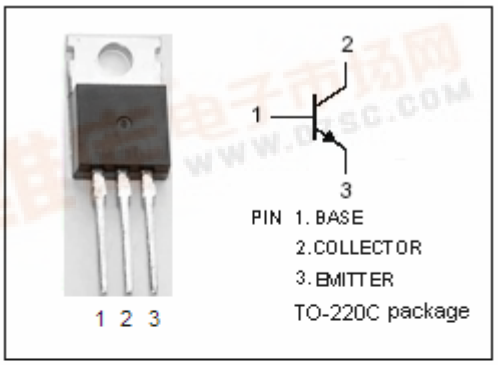
isc Silicon NPN Power Transistor 2SC1569



DESCRIPTION

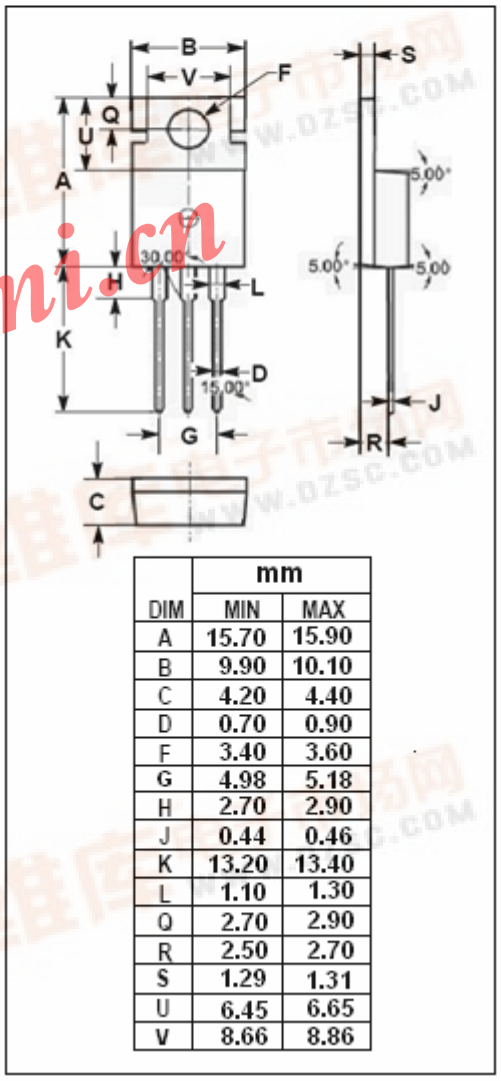
- High Collector-Emitter Breakdown Voltage-
  :$V_{(BR)CEO}$= 300V(Min)
- DC Current Gain-
  : h_{FE}= 40-170 @I_C= 50mA, V_{CE}= 10V
- High Current-Gain Bandwidth Product

APPLICATIONS

- Designed for color TV chroma output applications.

ABSOLUTE MAXIMUM RATINGS(T_a=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	300	V
V_{CEO}	Collector-Emitter Voltage	300	V
V_{EBO}	Emitter-Base Voltage	5	V
I_C	Collector Current-Continuous	150	mA
I_E	Emitter Current-Continuous	-150	mA
P_C	Collector Power Dissipation @ T_a=25℃	1.5	W
	Collector Power Dissipation @ T_C=25℃	12.5	
T_J	Junction Temperature	150	℃
T_{stg}	Storage Temperature Range	-55~150	℃



DIM	mm MIN	mm MAX
A	15.70	15.90
B	9.90	10.10
C	4.20	4.40
D	0.70	0.90
F	3.40	3.60
G	4.98	5.18
H	2.70	2.90
J	0.44	0.46
K	13.20	13.40
L	1.10	1.30
Q	2.70	2.90
R	2.50	2.70
S	1.29	1.31
U	6.45	6.65
V	8.66	8.86

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ELECTRICAL CHARACTERISTICS

T_C=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	I_C= 5mA ; I_B= 0	300			V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	I_C= 100mA; I_B= 20mA			1.0	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	I_C= 100mA; I_B= 20mA			1.2	V
I_{CBO}	Collector Cutoff Current	V_{CB}= 100V ; I_E= 0			1.0	μA
I_{EBO}	Emitter Cutoff Current	V_{EB}= 5V; I_C= 0			1.0	μA
h_{FE}	DC Current Gain	I_C= 50mA ; V_{CE}= 10V	40		170	
C_{OB}	Output Capacitance	I_E= 0; V_{CB}= 50V; f_{test}= 1MHz		5		pF
f_T	Current-Gain—Bandwidth Product	I_C= 30mA; V_{CE}= 10V	40			MHz